CPH3122



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Bipolar Transistor -30V, -3A, Low VCE(sat) PNP Single CPH3

Applications

· Relay drivers, lamp drivers, motor drivers, flash

Features

- · Adoption of MBIT processes
- · Large current capacity
- · Low collector to emitter saturation voltage
- High-speed switching
- Ultrasmall package facilitates miniaturization in end products (mounting height : 0.9mm)
- · High allowable power dissipation

Specifications

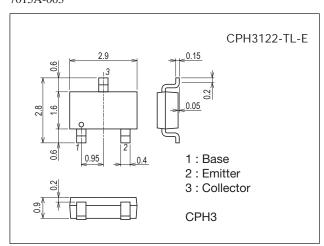
Absolute Maximum Ratings at Ta=25°C

3				
Parameter	Symbol	Conditions	Ratings	Unit
Collector to Base Voltage	VCBO		-30	V
Collector to Emitter Voltage	VCEO		-30	V
Emitter to Base Voltage	VEBO		-5	V
Collector Current	IC		-3	Α
Collector Current (Pulse)	ICP		-5	Α
Base Current	IB		-600	mA
Collector Dissipation	PC	When mounted on ceramic substrate (600mm ² ×0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7015A-003



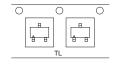
Product & Package Information

• Package : CPH3

• JEITA, JEDEC : SC-59, TO-236, SOT-23

• Minimum Packing Quantity : 3,000 pcs./reel

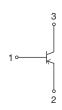
Packing Type: TL



Marking



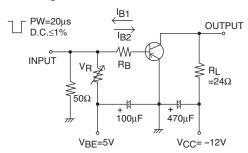
Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
Parameter		Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} = -30V, I _E =0A			-0.1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} = -4V, I _C =0A			-0.1	μΑ
DC Current Gain	hFE	V _{CE} = -2V, I _C = -500mA	200		560	
Gain-Bandwidth Product	fŢ	V _{CE} = -10V, I _C = -500mA		400		MHz
Output Capacitance	Cob	V _{CB} = -10V, f=1MHz		25		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)1	I _C = -1.5A, I _B = -30mA		-180	-270	mV
	V _{CE} (sat)2	I _C = -1.5A, I _B = -75mA		-120	-180	mV
Base to Emitter Saturation Voltage	V _{BE} (sat)	I _C = -1.5A, I _B = -30mA		-0.83	-1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	IC= -10μA, IE=0A	-30			V
Collector to Emitter Breakdown Voltage	V(BR)CEO	IC= -1mA, RBE=∞	-30			V
Emitter to Base Breakdown Voltage	V(BR)EBO	I _E = -10μA, I _C =0A	-5			V
Turn-ON Time	ton			50		ns
Storage Time	tstg	See specified Test Circuit.		270		ns
Fall Time	tf			27		ns

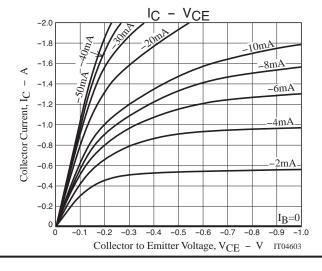
Switching Time Test Circuit

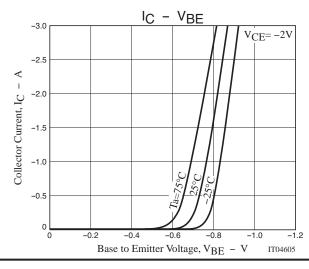


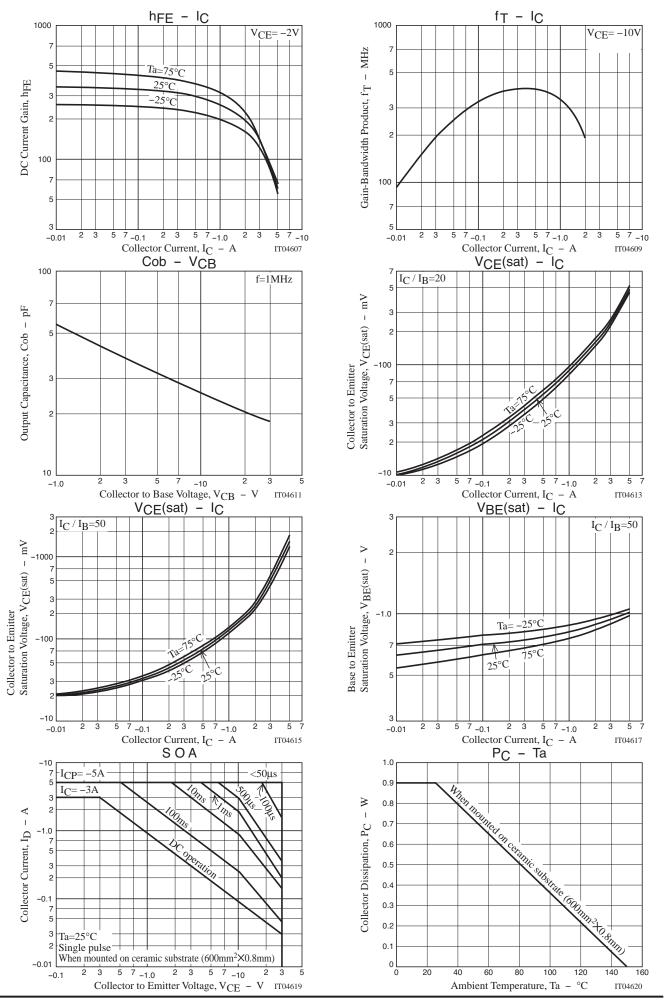
 $I_{C}=20I_{B1}=-20I_{B2}=-500mA$

Ordering Information

Device	Package	Shipping	memo	
CPH3122-TL-E	3122-TL-E CPH3		Pb Free	





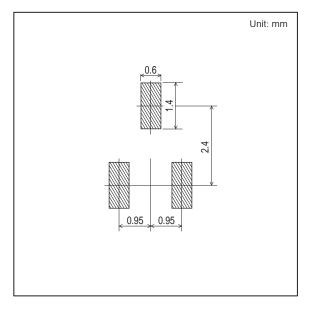


Outline Drawing

CPH3122-TL-E

Mass (g) Unit 0.013 mm 0.6±0.1 0, 2±0, 1 *1 *1 0. 05±0.05 6±0. *1 2 0.95 0.6±0. PIN#1 *1:Lot indication

Land Pattern Example



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